

Proposed Amendments to the Claims

It is requested that the following Listing of Claims replace all prior versions and listings of claims in the application:

Listing of Claims:

Claims 1-4 (cancelled)

Claim 5-7 (cancelled)

8. (Allowed, Currently Amended) A method of forming a bipolar transistor structure, the method comprising:
- forming a shallow trench isolated (STI) active device region in a silicon substrate;
 - forming a collector region of n-type conductivity in the STI active device region;
 - forming a lower layer of P-doped epitaxial SiGe material on the n-type collector region;
 - forming an upper layer of p-doped epitaxial SiGe material of the lower [payer] layer of SiGe material, the dopant concentration of the upper layer being at least about [minus] 10X [or less] lower than the dopant concentration of the lower layer; and
 - forming an n-doped polysilicon emitter region on the upper layer of SiGe material.
9. (Allowed) A method as in claim 8, and wherein the dopant concentration of the lower layer of SiGe material is about 1E19 and the dopant concentration of the upper layer of SiGe material is about 1E18.
10. (Allowed) A method as in claim 8, and wherein the p-type dopant in the lower layer of SiGe material comprises boron.
11. (Allowed) A method as in claim 10, and wherein the p-type dopant in the upper layer of SiGe material comprises boron.

12. (Allowed) A method as in claim 8, and wherein the dopant concentration in the upper layer of SiGe material is zero.

13. (New) A method as in claim 8, and wherein the dopant concentration in the upper layer of SiGe material is between 0 – 1E18.